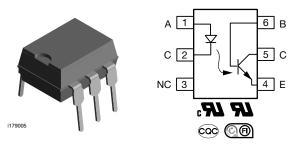


### Vishay Semiconductors

# **Optocoupler, Phototransistor Output, With Base Connection**



#### **FEATURES**

- Current transfer ratio (see order information)
- Isolation test voltage 4420 V<sub>RMS</sub>
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





### **LINKS TO ADDITIONAL RESOURCES**



#### **DESCRIPTION**

The IL2 is an optically coupled isolated pairs employing GaAs infrared LEDs and silicon NPN phototransistor. Signal information, including a DC level, can be transmitted by the drive while maintaining a high degree of electrical isolation between input and output. The IL2 is especially designed for driving medium-speed logic and can be used to eliminate troublesome ground loop and noise problems. This coupler can be used also to replace relays and transformers in many digital interface applications such as CRT modulation.

### **AGENCY APPROVALS**

- UL 1577
- cUL
- CQC GB4943.1
- CQC GB8898
- FIMKO

ORDERING INFORMATION	
PART NUMBER	PACKAGE OPTION  PACKAGE OPTION  PACKAGE OPTION  Option 9  Option 9
AGENCY CERTIFIED / PACKAGE	CTR (%)
UL, cUL, CQC, FIMKO	> 100
SMD-6, option 9	IL2-X009T

### Note

Additional options may be possible, please contact sales office

ABSOLUTE MAXIMUM RATINGS (T <sub>amb</sub> = 25 °C, unless otherwise specified)								
PARAMETER TEST CONDITION SYMBOL VALUE UNIT								
INPUT								
Reverse voltage		$V_R$	6	V				
Forward current		I <sub>F</sub>	60	mA				
Surge current		I <sub>FSM</sub>	2.5	Α				
Power dissipation		P <sub>diss</sub>	100	mW				
Derate linearly from 25 °C			1.33	mW/°C				



### Vishay Semiconductors

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>amb</sub> = 25 °C, unless otherwise specified)							
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT			
OUTPUT							
Collector emitter breakdown voltage		BV <sub>CEO</sub>	70	V			
Emitter base breakdown voltage		BV <sub>EBO</sub>	7	V			
Collector base breakdown voltage		BV <sub>CBO</sub>	70	V			
Collector current		I <sub>C</sub>	50	mA			
Collector current	t < 1.0 ms	I <sub>C</sub>	400	mA			
Power dissipation		P <sub>diss</sub>	200	mW			
Derate linearly from 25 °C			2.6	mW/°C			
COUPLER							
Package power dissipation		P <sub>tot</sub>	250	mW			
Derate linearly from 25 °C			3.3	mW/°C			
Storage temperature		T <sub>stg</sub>	-40 to +150	°C			
Operating temperature		T <sub>amb</sub>	-40 to +100	°C			
Junction temperature		Tj	125	°C			
Soldering temperature (1)	2.0 mm from case bottom	T <sub>sld</sub>	260	°C			

#### Notes

- Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not
  implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute
  maximum ratings for extended periods of the time can adversely affect reliability
- (1) Refer to reflow profile for soldering conditions for surface mounted devices (SMD). Refer to wave profile for soldering conditions for through hole devices (DIP)

PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
INPUT	·					
Forward voltage	I <sub>F</sub> = 60 mA	V <sub>F</sub>	=	1.25	1.65	V
Breakdown voltage	I <sub>R</sub> = 10 μA	$V_{BR}$	6	30	-	V
Reverse current	V <sub>R</sub> = 6.0 V	I <sub>R</sub>	=	0.01	10	μΑ
Capacitance	V <sub>R</sub> = 0 V, f = 1.0 MHz	Co	=	40	-	pF
Thermal resistance junction to lead		R <sub>thjl</sub>	-	750	-	K/W
OUTPUT	•					
Collector emitter capacitance	V <sub>CE</sub> = 5.0 V, f = 1.0 MHz	C <sub>CE</sub>	-	6.8	-	pF
Collector base capacitance	$V_{CB} = 5.0 \text{ V}, f = 1.0 \text{ MHz}$	C <sub>CB</sub>	-	8.5	-	pF
Emitter base capacitance	V <sub>EB</sub> = 5.0 V, f = 1.0 MHz	C <sub>EB</sub>	-	11	-	pF
Collector emitter leakage voltage	V <sub>CE</sub> = 10 V	I <sub>CEO</sub>	-	5	50	nA
Collector emitter saturation voltage	$I_{CE} = 1.0 \text{ mA}, I_{B} = 20 \mu\text{A}$	V <sub>CEsat</sub>	-	0.25	-	V
Base emitter voltage	$V_{CE} = 10 \text{ V}, I_B = 20 \mu\text{A}$	VBE	=	0.65	-	V
DC forward current gain	$V_{CE} = 10 \text{ V}, I_B = 20 \mu A$	h <sub>FE</sub>	200	650	1800	
DC forward current gain saturated	$V_{CE} = 0.4 \text{ V}, I_{B} = 20 \mu\text{A}$	h <sub>FEsat</sub>	120	400	600	
Thermal resistance junction to lead		R <sub>thjl</sub>	=	500	-	K/W
COUPLER						
Capacitance (input to output)	$V_{I-O} = 0 \text{ V, f} = 1.0 \text{ MHz}$	C <sub>IO</sub>	-	0.6	-	pF
Insulation resistance	V <sub>I-O</sub> = 500 V	R <sub>S</sub>	-	10 <sup>14</sup>	-	Ω

#### Note

Minimum and maximum values are testing requirements. Typical values are characteristics of the device and are the result of engineering
evaluation. Typical values are for information only and are not part of the testing requirements



# Vishay Semiconductors

CURRENT TRANSFER RATIO							
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT	
Current transfer ratio (collector emitter saturated)	$I_F = 10 \text{ mA}, V_{CE} = 0.4 \text{ V}$	CTR <sub>CEsat</sub>	-	170	-	%	
Current transfer ratio (collector emitter)	I <sub>F</sub> = 10 mA, V <sub>CE</sub> = 10 V	CTR <sub>CE</sub>	100	200	500	%	
Current transfer ratio (collector base)	$I_F = 10 \text{ mA}, V_{CB} = 9.3 \text{ V}$	CTR <sub>CB</sub>	-	0.25	-	%	

SWITCHING CHARACTERISTICS							
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT	
NON-SATURATED							
Current time	$V_{CE}$ = 5 V, $R_L$ = 75 $\Omega$ , $t_P$ measured at 50 % of output	I <sub>F</sub>	-	4	-	mA	
Delay time	$V_{CE}$ = 5 V, $R_L$ = 75 $\Omega$ , $t_P$ measured at 50 % of output	t <sub>D</sub>	-	1.7	-	μs	
Rise time	$V_{CE}$ = 5 V, $R_L$ = 75 $\Omega$ , $t_P$ measured at 50 % of output	t <sub>r</sub>	-	2.6	-	μs	
Storage time	$V_{CE}$ = 5 V, $R_L$ = 75 $\Omega$ , $t_P$ measured at 50 % of output	t <sub>s</sub>	-	0.4	-	μs	
Fall time	$V_{CE}$ = 5 V, $R_L$ = 75 $\Omega$ , $t_P$ measured at 50 % of output	t <sub>f</sub>	-	2.2	-	μs	
Propagation H to L	$V_{CE}$ = 5 V, $R_L$ = 75 $\Omega$ , $t_P$ measured at 50 % of output	t <sub>PHL</sub>	-	1.2	-	μs	
Propagation L to H	$V_{CE}$ = 5 V, $R_L$ = 75 $\Omega$ , $t_P$ measured at 50 % of output	t <sub>PLH</sub>	-	2.3	-	μs	
SATURATED	•						
Current time	$V_{CE} = 0.4 \text{ V}, R_L = 1.0 \text{ k}\Omega, \ V_{CL} = 5 \text{ V}, V_{TH} = 1.5 \text{ V}$	I <sub>F</sub>	-	5	-	mA	
Delay time	$V_{CE} = 0.4 \text{ V}, R_L = 1.0 \text{ k}\Omega, \ V_{CL} = 5 \text{ V}, V_{TH} = 1.5 \text{ V}$	t <sub>D</sub>	-	1	-	μs	
Rise time	$V_{CE} = 0.4 \text{ V}, R_L = 1.0 \text{ k}\Omega, \ V_{CL} = 5 \text{ V}, V_{TH} = 1.5 \text{ V}$	t <sub>r</sub>	-	2	-	μs	
Storage time	$V_{CE} = 0.4 \text{ V}, R_L = 1.0 \text{ k}\Omega, \ V_{CL} = 5 \text{ V}, V_{TH} = 1.5 \text{ V}$	t <sub>S</sub>	-	5.4	-	μs	
SATURATED	SATURATED						
Fall time	$V_{CE} = 0.4 \text{ V}, R_L = 1.0 \text{ k}\Omega, \ V_{CL} = 5 \text{ V}, V_{TH} = 1.5 \text{ V}$	t <sub>f</sub>	-	13.5	-	μs	
Propagation H to L	$V_{CE} = 0.4 \text{ V}, R_L = 1.0 \text{ k}\Omega, \ V_{CL} = 5 \text{ V}, V_{TH} = 1.5 \text{ V}$	t <sub>PHL</sub>	-	5.4	-	μs	
Propagation L to H	$V_{CE} = 0.4 \text{ V}, R_L = 1.0 \text{ k}\Omega, \ V_{CL} = 5 \text{ V}, V_{TH} = 1.5 \text{ V}$	t <sub>PLH</sub>	-	7.4	-	μs	

COMMON MODE TRANSIENT IMMUNITY						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Common mode rejection output high	$V_{CM} = 50 V_{P-P}, R_L = 1 k\Omega, I_F = 10 mA$	CM <sub>H</sub>	-	5000	-	V/µs
Common mode rejection output low	$V_{CM} = 50 V_{P-P}, R_L = 1 k\Omega, I_F = 10 mA$	CM <sub>L</sub>	-	5000	-	V/µs
Common mode coupling capacitance		C <sub>CM</sub>	-	0.01	-	pF



# Vishay Semiconductors

SAFETY AND INSULATION RATINGS				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Climatic classification	According to IEC 68 part 1		40 / 100 / 21	
Comparative tracking index		CTI	175	
Maximum rated withstanding isolation voltage	t = 1 min	V <sub>ISO</sub>	4420	$V_{RMS}$
Maximum transient isolation voltage		V <sub>IOTM</sub>	10 000	V <sub>peak</sub>
Maximum repetitive peak isolation voltage		V <sub>IORM</sub>	890	V <sub>peak</sub>
Indiate well-to-	V <sub>IO</sub> = 500 V, T <sub>amb</sub> = 25 °C	R <sub>IO</sub>	≥ 10 <sup>12</sup>	Ω
Isolation resistance	V <sub>IO</sub> = 500 V, T <sub>amb</sub> = 100 °C	R <sub>IO</sub>	≥ 10 <sup>11</sup>	Ω
Output safety power		P <sub>SO</sub>	400	mW
Input safety current		I <sub>SI</sub>	275	mA
Safety temperature		T <sub>S</sub>	175	°C
Creepage distance			≥ 7	mm
Clearance distance			≥ 7	mm
Insulation thickness		DTI	≥ 0.4	mm

#### Note

<sup>•</sup> As per IEC 60747-5-5, § 7.4.3.8.2, this optocoupler is suitable for "safe electrical insulation" only within the safety ratings. Compliance with the safety ratings shall be ensured by means of protective circuits

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### Vishay Semiconductors

### TYPICAL CHARACTERISTICS (T<sub>amb</sub> = 25 °C, unless otherwise specified)

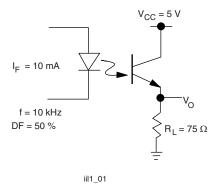


Fig. 1 - Non-Saturated Switching Schematic

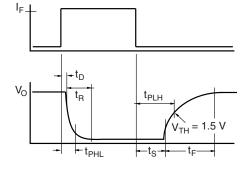


Fig. 4 - Saturated Switching Timing

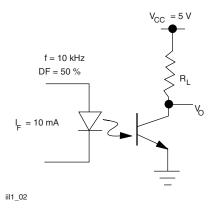


Fig. 2 - Saturated Switching Schematic

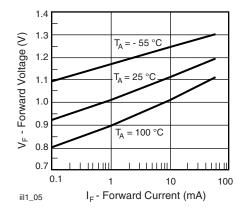


Fig. 5 - Forward Voltage vs. Forward Current

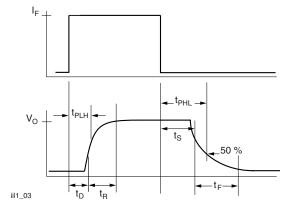


Fig. 3 - Non-Saturated Switching Timing

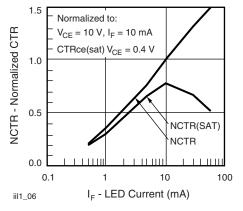


Fig. 6 - Normalized Non-Saturated and Saturated CTR vs. LED Current



## Vishay Semiconductors

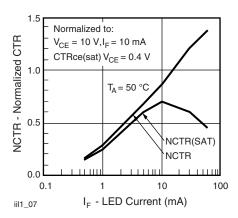


Fig. 7 - Normalized Non-Saturated and Saturated CTR vs. LED Current

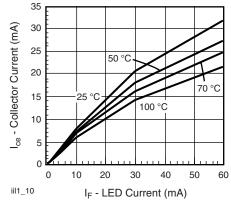


Fig. 10 - Collector Emitter Current vs. Temperature and LED Current

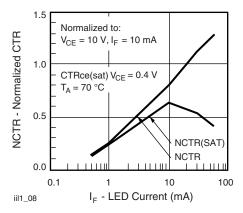


Fig. 8 - Normalized Non-Saturated and Saturated CTR vs. LED Current

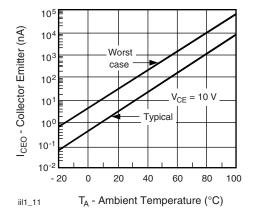


Fig. 11 - Collector Emitter Leakage Current vs. Temperature

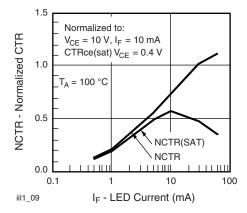


Fig. 9 - Normalized Non-Saturated and Saturated CTR,  $T_{amb} = 100~^{\circ}\text{C}$  vs. LED Current

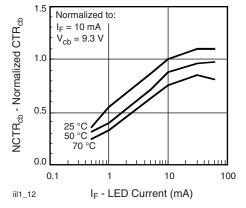


Fig. 12 - Normalized  $CTR_{cb}$  vs. LED Current and Temperature



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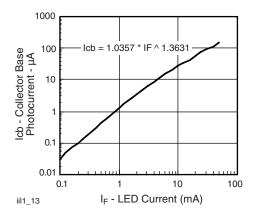


Fig. 13 - Collector Base Photocurrent vs. LED Current

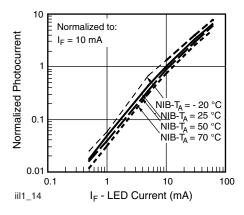


Fig. 14 - Normalized Photocurrent vs. I<sub>F</sub> and Temperature

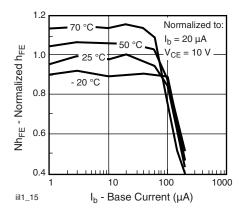


Fig. 15 - Normalized Non-Saturated  $h_{\text{FE}}$  vs. Base Current and Temperature

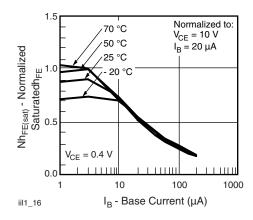


Fig. 16 - Normalized Saturated h<sub>FE</sub> vs. Base Current and Temperature

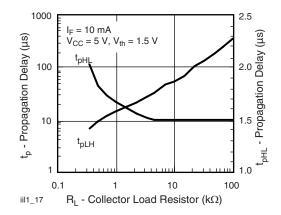
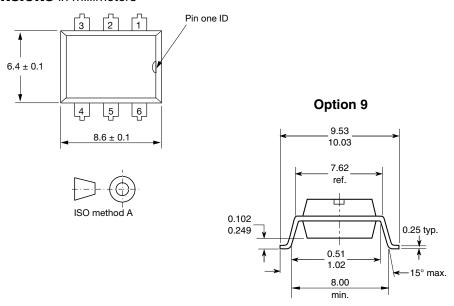


Fig. 17 - Propagation Delay vs. Collector Load Resistor

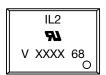


# Vishay Semiconductors

### **PACKAGE DIMENSIONS** in millimeters



### **PACKAGE MARKING**



#### Note

• XXXX = LMC (lot marking code)



### **Legal Disclaimer Notice**

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